

STB180N55F3 STP180N55F3

N-channel 55V - 3.2mΩ - 120A - D²PAK/TO-220 STripFET™ Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)}	I _D	Pw
STB180N55F3	55V	3.5 m Ω	120A ⁽¹⁾	330W
STP180N55F3	55V	3.8 m Ω	120A ⁽¹⁾	330W

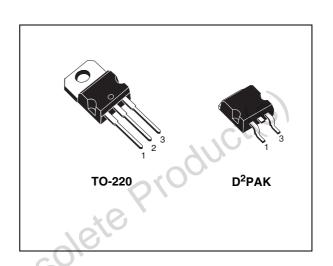
- 1. Value limited by wire bonding
- Ultra low on-resistance
- 100% avalanche tested

Description

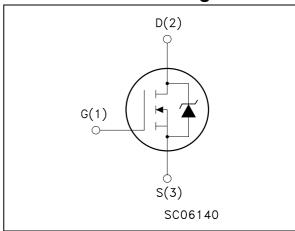
This n-channel enhancement mode Power MOSFET is the latest refinement of STMicroelectronics unique "single feature size™" strip-based process with less critical alignment steps and therefore a remarkable manufacturing reproducibility. The resulting transistor shows extremely high packing density for low on resistance, rugged avalanche characteristics and low gate charge.

Application

Switching applications



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB180N55F3	180N55F3	D ² PAK	Tape & reel
STP180N55F3	180N55F3	TO-220	Tube

June 2007 Rev 2 1/14

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} =0)	55	V
V_{GS}	Gate-source voltage	± 20	V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25°C	120	Α
I _D ⁽¹⁾	Drain current (continuous) at T _C =100°C	120	Α
I _{DM} ⁽²⁾	Drain current (pulsed)	480	O A
P _{TOT}	Total dissipation at T _C = 25°C	330	W
	Derating factor	2.2	W/°C
dv/dt (3)	Peak diode recovery voltage slope	11	V/ns
E _{AS} (4)	Single pulse avalanche energy	1000	mJ
T _j T _{stg}	Operating junction temperature storage temperature	-55 To 175	°C

- 1. Current limited by package.
- 2. Pulse width limited by safe operating area.
- 3. $I_{SD} \leq 120A$, $di/dt \leq 900A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$
- 4. Starting Tj=25°C, Id=60A, Vdd=40V (see Figure 15 and Figure 16)

Table 2. Thermal data

Symbol	Parameter	TO-220	D ² PAK	Unit
Rthj-case	Thermal resistance junction-case	0.4	°C/W	
Rthj-a	Thermal resistance junction-ambient max	62.5		°C/W
Rthj-pcb ⁽¹⁾	Thermal resistance junction-ambient max		50	°C/W
T _I	Maximum lead temperature for soldering purpose	300		°C

1. When mounted on FR-4 board, on 1inch², 2oz Cu.

Electrical characteristics 2

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	55			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = max rating, V _{DS} = max rating,@125°C			10 100	μ Α μ Α
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20V			±200	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	AU	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 60A D ² PAK TO-220	610	2.9 3.2	3.5 3.8	m Ω
Table 4.	Dynamic	coleite				
		10.3				

Table 4. **Dynamic**

		2 y name						
	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
	9 _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15V _, I _D = 60A		150		S	
	C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V$, $f = 1MHz$, $V_{GS} = 0$		6800 1450 15		pF pF pF	
7/6	$\begin{matrix} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \end{matrix}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 27.5V, I_D = 60A R_G = 4.7 Ω V_{GS} = 10V (see Figure 12, Figure 17)		25 150 110 50		ns ns ns ns	
90.	Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 44V$, $I_D = 120A$, $V_{GS} = 10V$, (see Figure 13)		100 30 26		nC nC nC	
	1 Dulandi D	Duland, Dulan duration, 200 up duty qual 1.59/						

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

Table 5. Source drain diode

14510 01						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current				120	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				480	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} =120A, V _{GS} =0			1.5	V
t _{rr}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} =120A, di/dt = 100A/μs, V _{DD} =35V, Tj=150°C (see <i>Figure 14</i>)		60 0.11 3.5		ns µC A
1. Pulse wid	Reverse recovery current th limited by safe operating area ulse duration = 300µs, duty cycle	(See Figure 14)		<u> </u>	1/5	
2. Pulsed: p	ulse duration = 300µs, duty cycle	e 1.5%		1	Cri	
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2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

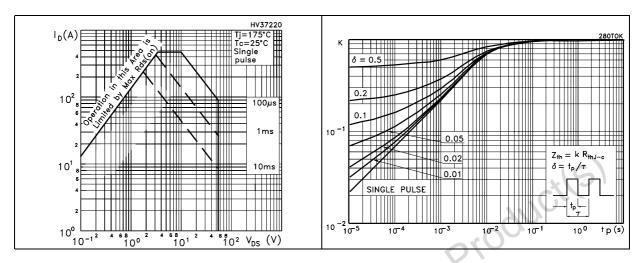


Figure 3. Output characteristics

Figure 4. Transfer characteristics

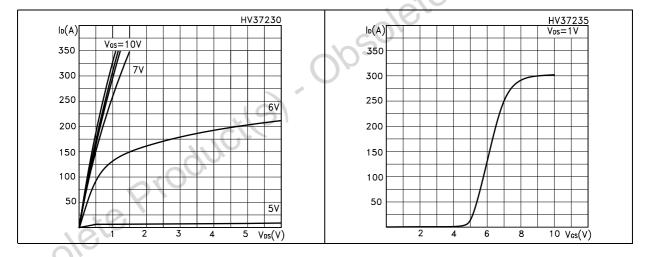


Figure 5. Normalized B_{VDSS} vs temperature

Figure 6. Static drain-source on resistance

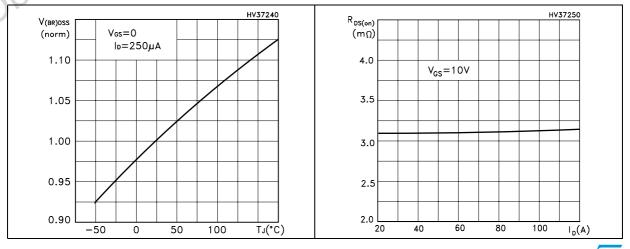


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

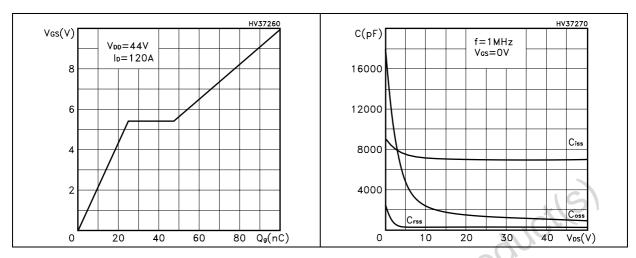


Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on resistance vs temperature

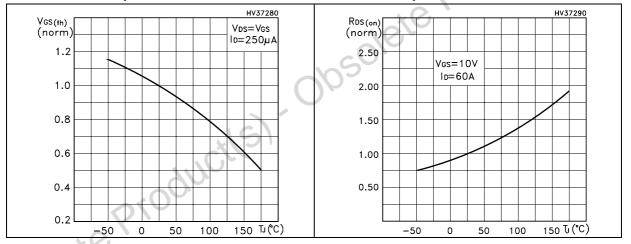
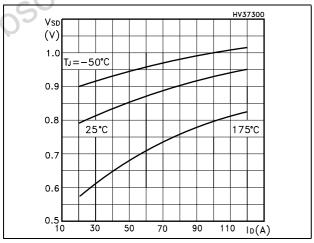


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

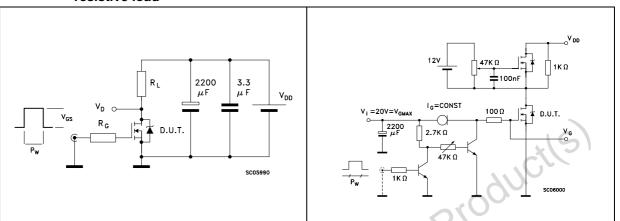


Figure 14. Test circuit for inductive load switching and diode recovery times

Figure 15. Unclamped Inductive load test circuit

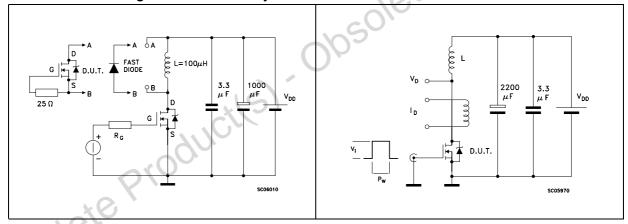
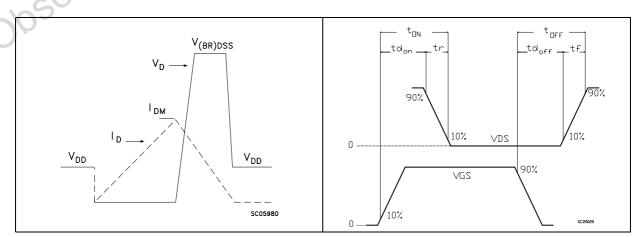


Figure 16. Unclamped inductive waveform

Figure 17. Switching time waveform



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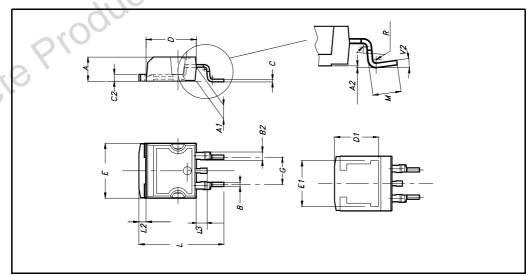
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s). Obsolete Product(s)

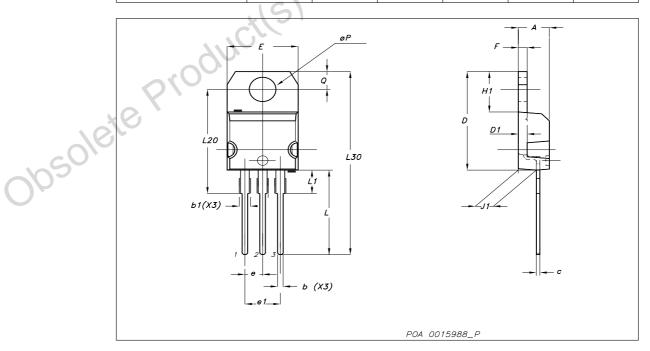
D²PAK MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352	YO	0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5		×0,	0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4	1	3.2	0.094		0.126
R	. 1	0.4			0.015	
V2	0º		4º			



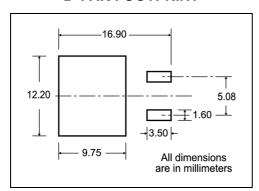
TO-220 mechanical data

Dim		mm			inch		
DIM	Min	Тур	Max	Min	Тур	Max	
Α	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.14		1.70	0.044		0.066	
С	0.49		0.70	0.019		0.027	
D	15.25		15.75	0.6	\vec{c}	0.62	
D1		1.27			0.050		
Е	10		10.40	0.393	40	0.409	
е	2.40		2.70	0.094	70.	0.106	
e1	4.95		5.15	0.194		0.202	
F	1.23		1.32	0.048		0.051	
H1	6.20		6.60	0.244		0.256	
J1	2.40		2.72	0.094		0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40)		0.645		
L30		28.90			1.137		
ØP	3.75		3.85	0.147		0.151	
Q	2.65		2.95	0.104		0.116	

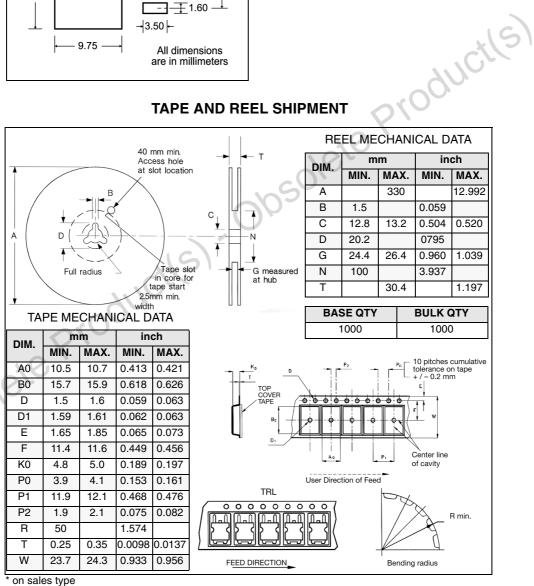


Packaging mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 6. Revision history

Date	Revision	Changes
31-Jan-2007	1	First version
01-Jun-2007	2	Complete version

Obsolete Product(s). Obsolete Product(s)

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